

N-channel 30 V 13.6 mΩ logic level MOSFET in LFPAK33 using NextPower Technology

23 February 2018

Product data sheet

1. General description

Logic level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- · Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

3. Applications

- DC-to-DC converters
- Load switching
- Synchronous buck regulator

4. Quick reference data

| Table 1. Quid | ck reference data | | | | | _ |
|---------------------|----------------------------------|--|-----|-------|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Мах | Unit |
| V _{DS} | drain-source voltage | T _j = 25 °C | - | - | 30 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | - | - | 39 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | - | - | 38 | W |
| Tj | junction temperature | | -55 | - | 175 | °C |
| Static chara | acteristics | · | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C; Fig. 10 | - | 14.65 | 16.9 | mΩ |
| | | V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 10 | - | 11.8 | 13.6 | mΩ |
| Dynamic ch | aracteristics | ' | | | | |
| Q_{GD} | gate-drain charge | I_D = 10 A; V_{DS} = 15 V; V_{GS} = 4.5 V; Fig. 12; Fig. 13 | - | 1 | - | nC |
| Q _{G(tot)} | total gate charge | I_D = 10 A; V_{DS} = 15 V; V_{GS} = 10 V; Fig. 12; Fig. 13 | - | 8 | - | nC |

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5. Pinning information

| Table 0 Dissing information | |
|------------------------------|--|
| Table 2. Pinning information | |

| Pin | Symbol | Description | Simpl | ified outline | | Graphic symbol |
|-----|--------|-----------------------------------|-------|-----------------------------|---|----------------|
| 1 | S | source | Í | | | D |
| 2 | S | source | | | | |
| 3 | S | source | | \bigcirc | | G |
| 4 | G | gate | | | | mbb076 S |
| mb | D | mounting base; connected to drain | | 1 2 3 4 FPAK33 (SOT1210) |) | |

6. Ordering information

| Table 3. Ordering information | | | | | | | |
|-------------------------------|---------|---|---------|--|--|--|--|
| Type number | Package | | | | | | |
| | Name | Description | Version | | | | |
| PSMN013-30MLC | LFPAK33 | Plastic single ended surface mounted package (LFPAK33); 8 leads | SOT1210 | | | | |

7. Marking

| Table 4. Marking codes | | | | |
|------------------------|---------------|--------------|--|--|
| | Type number | Marking code | | |
| | PSMN013-30MLC | M13C30 | | |

8. Limiting values

Table 5. Limiting values

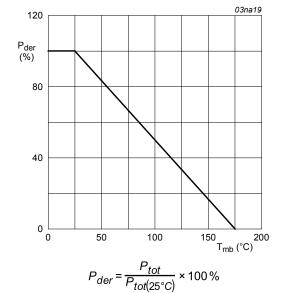
In accordance with the Absolute Maximum Rating System (IEC 60134).

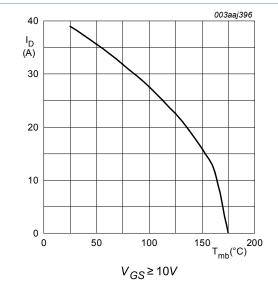
| Symbol | Parameter | Conditions | Min | Max | Unit |
|---------------------|----------------------------|---|-----|-----|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | - | 30 | V |
| V _{GS} | gate-source voltage | | -20 | 20 | V |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | - | 38 | W |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | - | 39 | А |
| | | V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u> | - | 28 | А |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3 | - | 157 | А |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | -55 | 175 | °C |
| T _{sld(M)} | peak soldering temperature | | - | 260 | °C |

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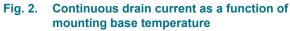
| Symbol | Parameter | Conditions | Min | Max | Unit | |
|----------------------|---|---|-----|-----|------|--|
| V _{ESD} | electrostatic discharge voltage | MM (JEDEC) | 100 | - | V | |
| Source-drain d | Source-drain diode | | | | | |
| I _S | source current | T _{mb} = 25 °C | - | 34 | А | |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | - | 157 | А | |
| Avalanche rug | Avalanche ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | $\label{eq:ld} \begin{array}{l} I_D = 39 \; A; V_{sup} \leq \; 30 \; V; R_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^\circ C; \; unclamped; \\ \hline Fig. \; 4 \end{array}$ | - | 5.6 | mJ | |

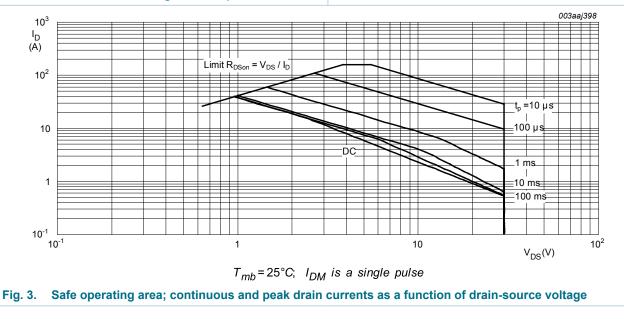






function of mounting base temperature

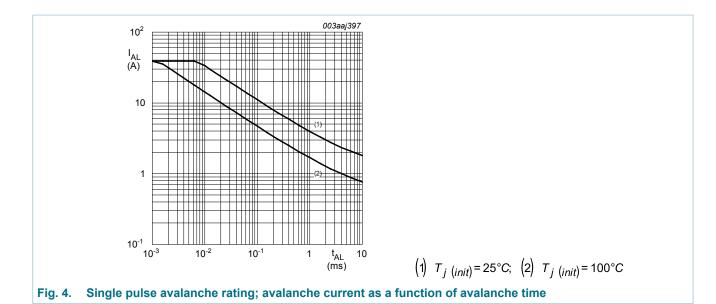




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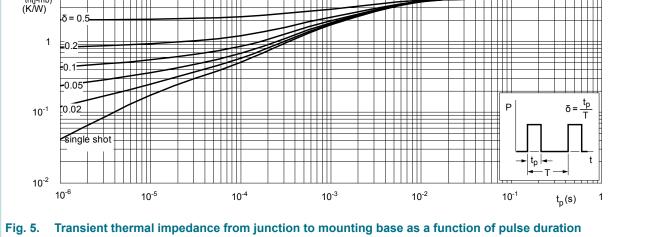
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9. Thermal characteristics

Table 6. Thermal characteristics Symbol Parameter Conditions Unit Min Тур Max thermal resistance Fig. 5 3.8 3.99 K/W R_{th(j-mb)} from junction to mounting base 003aaj399 10 Z_{th(j-mb)} (K/W) δ=0. 1 0.2



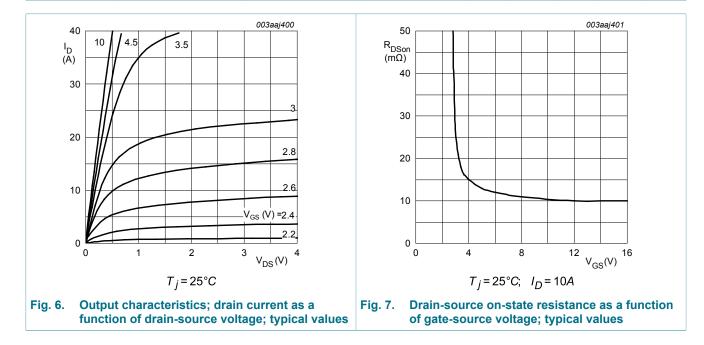
10. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------------|--|--|------|-------|-------|------|
| Static charac | cteristics | | | | | |
| V _{(BR)DSS} | drain-source | I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C | 30 | - | - | V |
| | breakdown voltage | I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C | 27 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ | 1.3 | 1.66 | 1.95 | V |
| ΔV _{GS(th)} /ΔT | gate-source threshold voltage variation with temperature | | - | -4 | - | mV/K |
| I _{DSS} | drain leakage current | V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 °C | - | - | 1 | μA |
| | | V _{DS} = 30 V; V _{GS} = 0 V; T _j = 150 °C | - | - | 100 | μA |
| I _{GSS} | gate leakage current | V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 100 | nA |
| | | V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 4.5 V; I _D = 10 A; T _j = 25 °C; <u>Fig. 10</u> | - | 14.65 | 16.9 | mΩ |
| | | V _{GS} = 4.5 V; I _D = 10 A; T _j = 150 °C; Fig. 10; Fig. 11 | - | - | 28.75 | mΩ |
| | | V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 10 | - | 11.8 | 13.6 | mΩ |
| | | V _{GS} = 10 V; I _D = 10 A; T _j = 150 °C; Fig. 10; Fig. 11 | - | - | 22.95 | mΩ |
| R _G | gate resistance | f = 1 MHz | 0.85 | 1.7 | 3.4 | Ω |
| Dynamic cha | aracteristics | | | | | |
| Q _{G(tot)} | total gate charge | I _D = 10 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 12; Fig. 13 | - | 8 | - | nC |
| | | I_D = 10 A; V_{DS} = 15 V; V_{GS} = 4.5 V; Fig. 12; Fig. 13 | - | 3.7 | - | nC |
| | | I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V | - | 7.4 | - | nC |
| Q _{GS} | gate-source charge | I_D = 10 A; V_{DS} = 15 V; V_{GS} = 4.5 V; | - | 1.2 | - | nC |
| Q _{GS(th)} | pre-threshold gate- source charge | Fig. 12; Fig. 13 | - | 0.8 | - | nC |
| Q _{GS(th-pl)} | post-threshold gate- source charge | | - | 0.4 | - | nC |
| Q _{GD} | gate-drain charge | | - | 1 | - | nC |
| V _{GS(pl)} | gate-source plateau voltage | I _D = 10 A; V _{DS} = 15 V; <u>Fig. 12</u> ; <u>Fig. 13</u> | - | 2.6 | - | V |
| C _{iss} | input capacitance | V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz; | - | 519 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C; <u>Fig. 14</u> | - | 131 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 37 | - | pF |

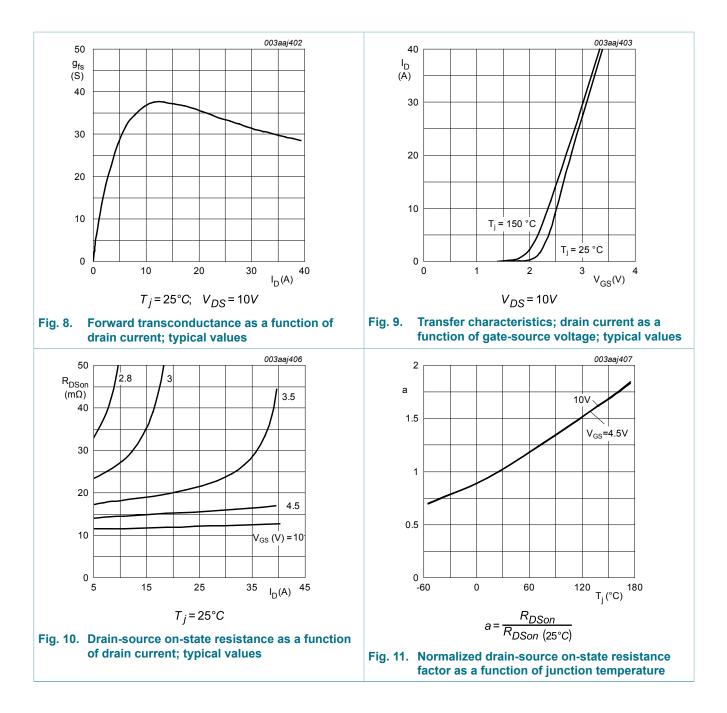
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| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|---------------------|----------------------------|--|--|-----|------|-----|------|
| t _{d(on)} | turn-on delay time | V_{DS} = 15 V; R_{L} = 1.5 Ω ; V_{GS} = 4.5 V; | | - | 7 | - | ns |
| t _r | rise time | $R_{G(ext)} = 5 \Omega$ | | - | 9.8 | - | ns |
| t _{d(off)} | turn-off delay time | | | - | 9.6 | - | ns |
| t _f | fall time | | | - | 5.5 | - | ns |
| Q _{oss} | output charge | V _{GS} = 0 V; V _{DS} = 15 V; f = 1 MHz; T _j = 25 °C | | - | 3.7 | - | nC |
| Source-dra | in diode | | | | | | |
| V _{SD} | source-drain voltage | I_{S} = 10 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 15</u> | | - | 0.86 | 1.1 | V |
| t _{rr} | reverse recovery time | I_{S} = 10 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V; | | - | 13.4 | - | ns |
| Q _r | recovered charge | V _{DS} = 15 V | | - | 6.6 | - | nC |
| t _a | reverse recovery rise time | $I_{S} = 10 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 15 \text{ V}; \underline{\text{Fig. 16}}$ | | - | 8.6 | - | ns |
| t _b | reverse recovery fall time | | | - | 4.8 | - | ns |

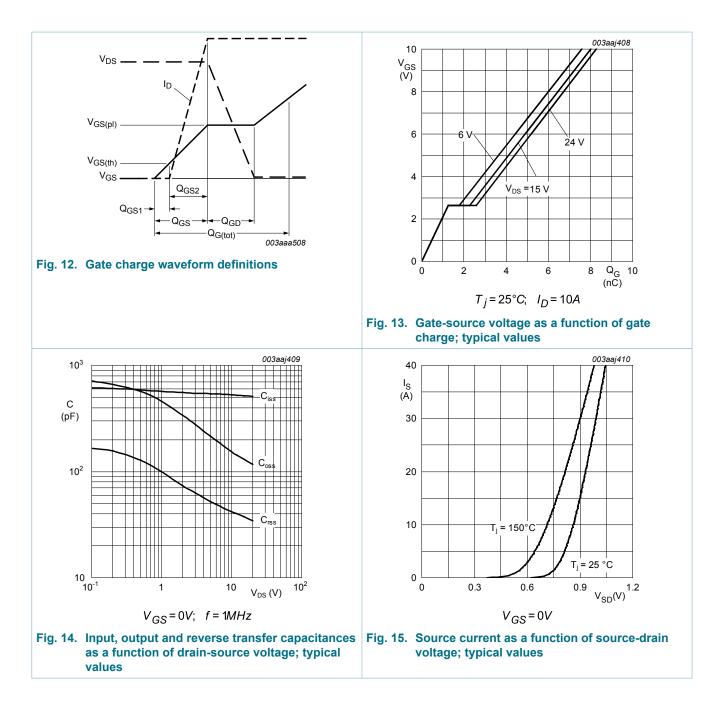


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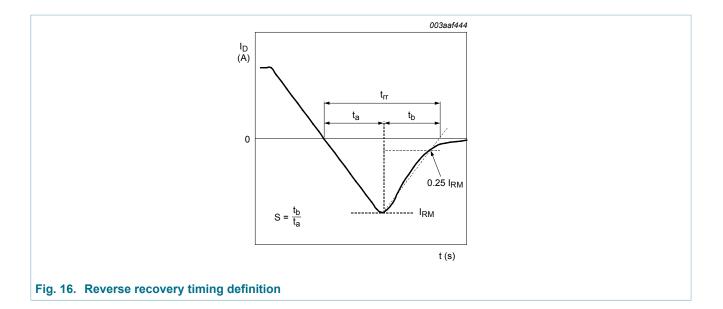
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11. Package outline

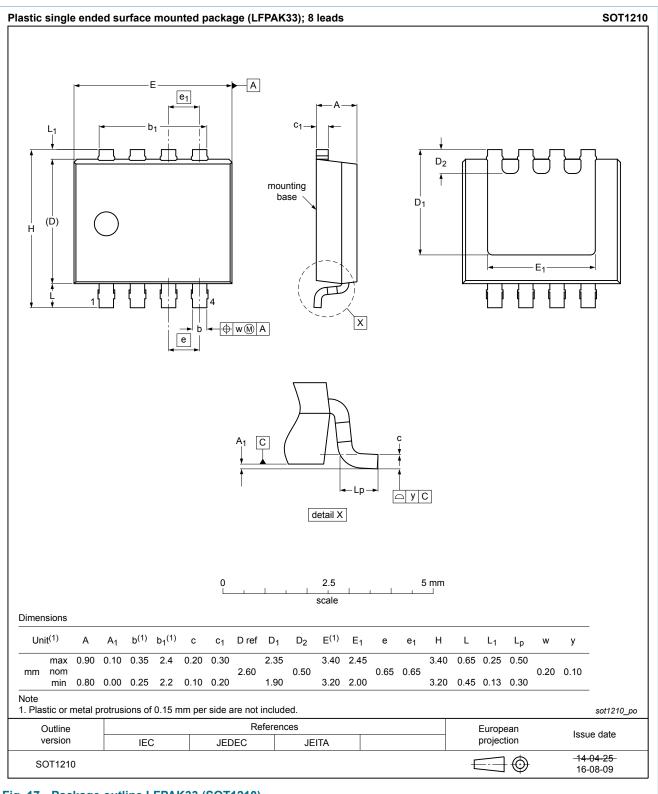
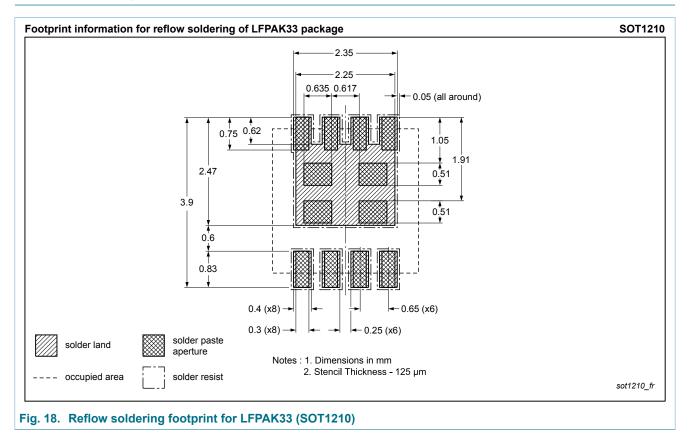


Fig. 17. Package outline LFPAK33 (SOT1210)

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12. Soldering



13. Legal information

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|--------------------------------------|-----------------------|---|
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